

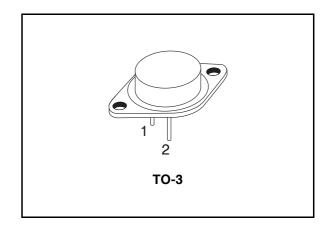
High power NPN silicon transistor

General features

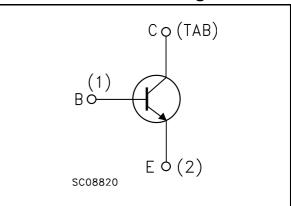
■ STMicroelectronics preferred salestype

Description

The device is a silicon planar NPN transistor mounted in Jedec TO-3 metal case. It is intended for linear amplifiers and inductive switching applications.



Internal schematic diagram



Order codes

Part Number	Marking	Package	Packing
2N3773	2N3773	TO-3	Bag

Electrical ratings 2N3773

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CEO}	Collector-emitter voltage (I _B = 0)	140	V
V _{CEV}	Collector-emitter voltage (V _{BE} = -1.5V)	160	V
V _{CBO}	Collector-base voltage (I _E = 0)	160	V
V _{EBO}	Emitter-base voltage ($I_C = 0$)	7	V
I _C	Collector current	16	Α
I _{CM}	Collector peak current (t _P < 5ms)	30	Α
I _B	Base current	4	Α
I _{BM}	Base peak current (t _P < 1ms)		Α
P _{tot}	Total dissipation at T _c ≤ 25°C	150	W
T _{stg}	Storage temperature	-65 to 200	°C

Table 2. Thermal data

Symbol	Parameter	Value	Unit	
R _{thj-case}	Thermal resistance junction-case	Max	1.17	°C/W

2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$

Table 3. Electrical characteristics

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I _{CEV}	Collector cut-off current (V _{BE} = -1.5V)	V _{CB} = 140V V _{CB} = 140V	T _j = 150°C			2 10	mA mA
I _{CEO}	Collector cut-off current (I _B = 0)	V _{CB} = 120V				10	mA
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = 140V				2	mA
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{CB} = 7V				5	mA
V _{CEO(sus)} (1)	Collector-emitter sustaining voltage (I _B = 0)	I _C = 0.2A		140			V
V _{CEV(sus)} (1)	Collector-emitter sustaining voltage (V _{EB} = -1.5V)	I _C = 0.2A		160			V
V _{CER(sus)} (1)	Collector-emitter sustaining voltage (R _{BE} = 100Ω)	I _C = 0.2A		150			V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	I _C = 8A I _C = 16A	_			1.4 4	V V
V _{BE} ⁽¹⁾	Base-emitter voltage	I _C = 8A	V _{CE} = 4V			2.2	V
h _{FE} ⁽¹⁾	DC current gain	I _C = 8A I _C = 16A	V _{CE} = 4V V _{CE} = 4V	15 5		60	
I _{s/b}	Second Breakdown Collector Current	V _{CE} = 30V t = 1s (non rep	petitive)	5			А

^{1.} Pulsed: Pulse duration = 300 μ s, duty cycle \leq 2 %

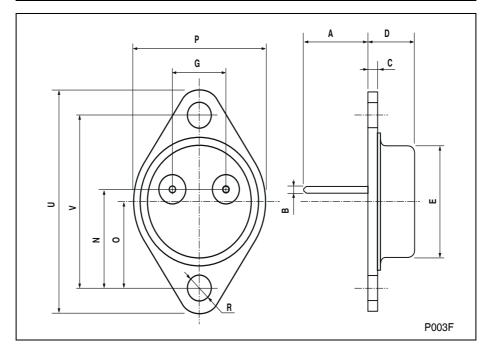
577

3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-3 MECHANICAL DATA

DIM.	mm			inch			
Diw.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α	11.00		13.10	0.433		0.516	
В	0.97		1.15	0.038		0.045	
С	1.50		1.65	0.059		0.065	
D	8.32		8.92	0.327		0.351	
E	19.00		20.00	0.748		0.787	
G	10.70		11.10	0.421		0.437	
N	16.50		17.20	0.649		0.677	
Р	25.00		26.00	0.984		1.023	
R	4.00		4.09	0.157		0.161	
U	38.50		39.30	1.515		1.547	
V	30.00		30.30	1.187		1.193	



577

Revision history 2N3773

4 Revision history

Table 4. Revision history

Date	Revision	Changes
03-Apr-2006	1	Initial release.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZE REPRESENTATIVE OF ST, ST PRODUCTS ARE NOT DESIGNED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS, WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2006 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

